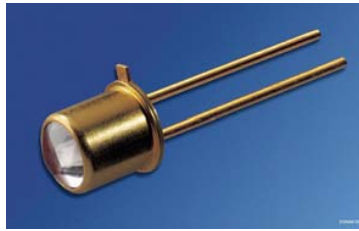


IR-Lumineszenzdiode (950 nm) im TO-46-Gehäuse
Infrared Emitter (950 nm) in TO-46 Package
Lead (Pb) Free Product - RoHS Compliant

SFH 4811
SFH 4813



SFH 4811



SFH 4813

Wesentliche Merkmale

- Hergestellt im Schmelzepitaxieverfahren
- Kathode galvanisch mit dem Gehäuseboden verbunden
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Hermetisch dichtes Metallgehäuse

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- IR-Gerätefernsteuerungen
- Sensorik
- Lichtgitter

Features

- Fabricated in a liquid phase epitaxy process
- Cathode is electrically connected to the case
- High reliability
- Matches all Si-Photodetectors
- Hermetically sealed package

Applications

- Photointerrupters
- IR remote control
- Sensor technology
- Light curtains

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 4811	Q62702P5300	TO-46-Metallgehäuse, Glaslinse, hermetisch dicht, Anschlüsse im 2.54-mm-Raster ($1/10''$) TO-46-metal-package, glass lens, hermetically sealed, solder tabs lead spacing 2.54 mm ($1/10''$)
SFH 4813	Q62702P5301	

Grenzwerte ($T_C = 25\text{ °C}$)
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlaßstrom Forward current	I_F	300	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	3	A
Verlustleistung Power dissipation	P_{tot}	470	mW
Wärmewiderstand Thermal resistance	R_{thJA} R_{thJC}	450 160	K/W K/W

Kennwerte ($T_A = 25\text{ °C}$)
Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle SFH 4811 SFH 4813	φ φ	± 5 ± 35	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²

Kennwerte ($T_A = 25\text{ °C}$) (cont'd)

Characteristics

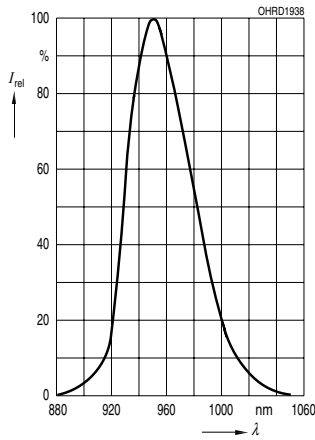
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top SFH 4811 SFH 4813	H H	4.7 2.6	mm mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$	t_r, t_f	0.5	μs
Kapazität Capacitance $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_o	25	pF
Durchlaßspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$ $I_F = 1.5\text{ A}$, $t_p = 100\ \mu\text{s}$	V_F V_F V_F	1.30 (≤ 1.5) 1.90 (≤ 2.5) 2.30 (≤ 3.0)	V V V
Sperrstrom Reverse current $V_R = 5\text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluß Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	8	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.55	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.3	nm/K

Gruppierung der Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01$ sr**Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01$ sr

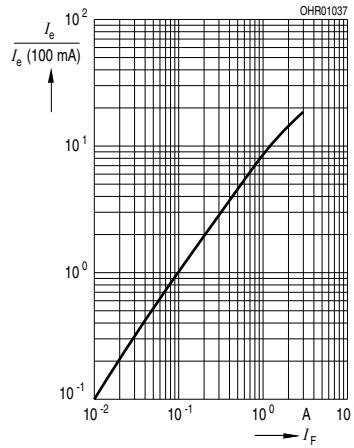
Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 4811	SFH 4813	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min.}}$	25	2.5	mW/sr
	$I_{e \text{ typ.}}$	40	4.5	mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	250	30	mW/sr

Relative Spectral Emission

$I_{rel} = f(\lambda)$

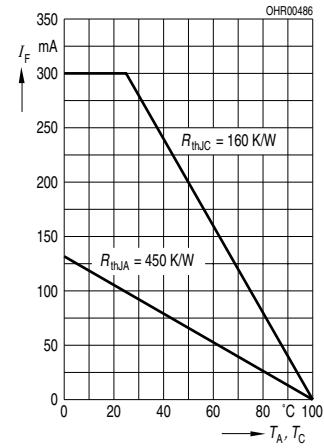


Radiant Intensity $I_e/I_e(100 \text{ mA}) = f(I_F)$
Single pulse, $t_p = 20 \mu\text{s}$



Max. Permissible Forward Current

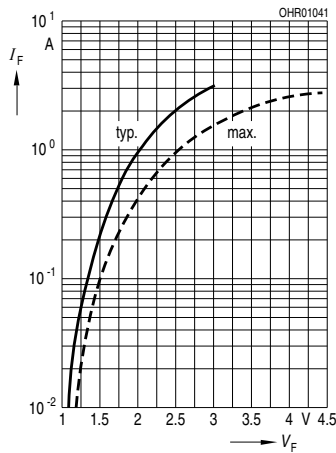
$I_F = f(T_A, T_C)$



Forward Current

$I_F = f(V_F)$

Single pulse, $t_p = 20 \mu\text{s}$

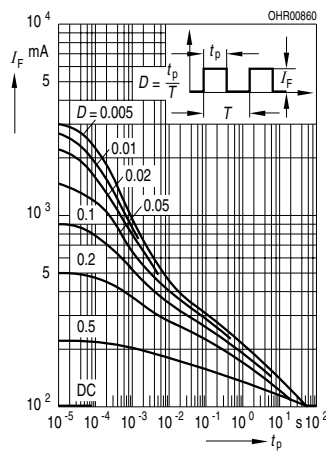


Permissible Pulse Handling Capability

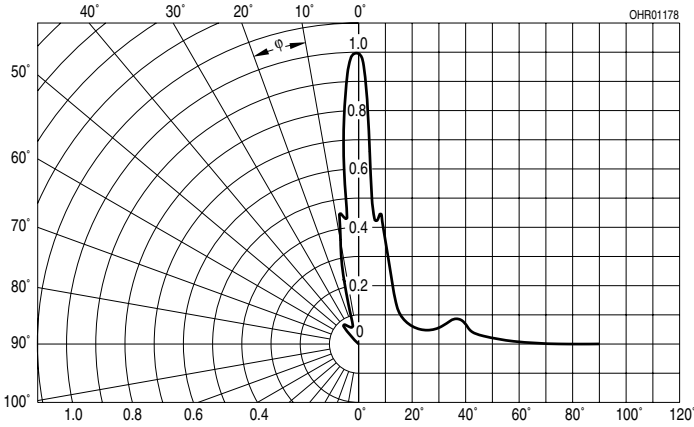
$I_F = f(\tau), T_C = 25 \text{ }^\circ\text{C}$,

$R_{thJC} = 160 \text{ K/W}$, duty cycle

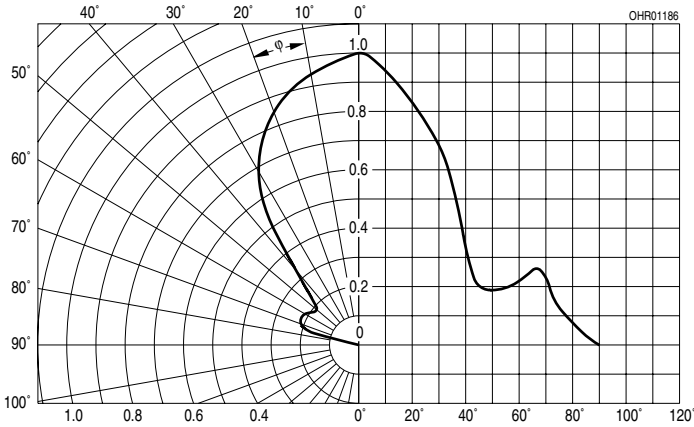
$D =$ parameter



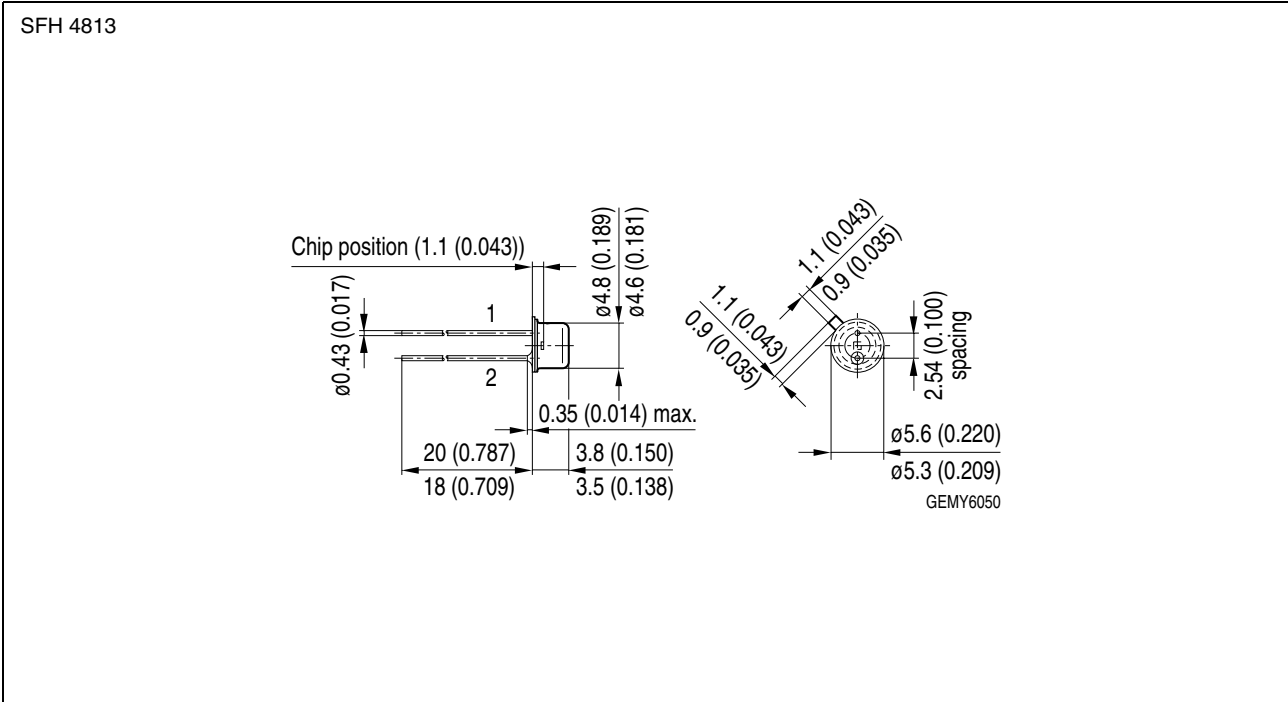
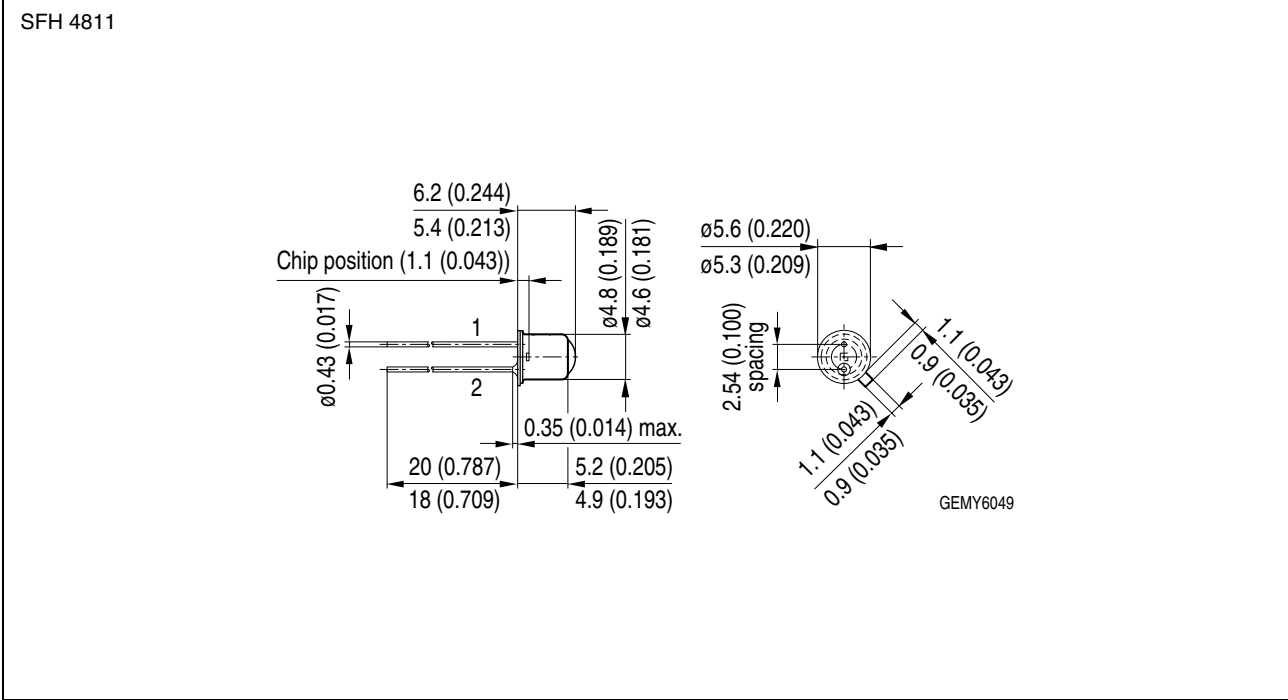
Radiation Characteristics, SFH 4811 $I_{rel} = f(\varphi)$



Radiation Characteristics, SFH 4813 $I_{rel} = f(\varphi)$



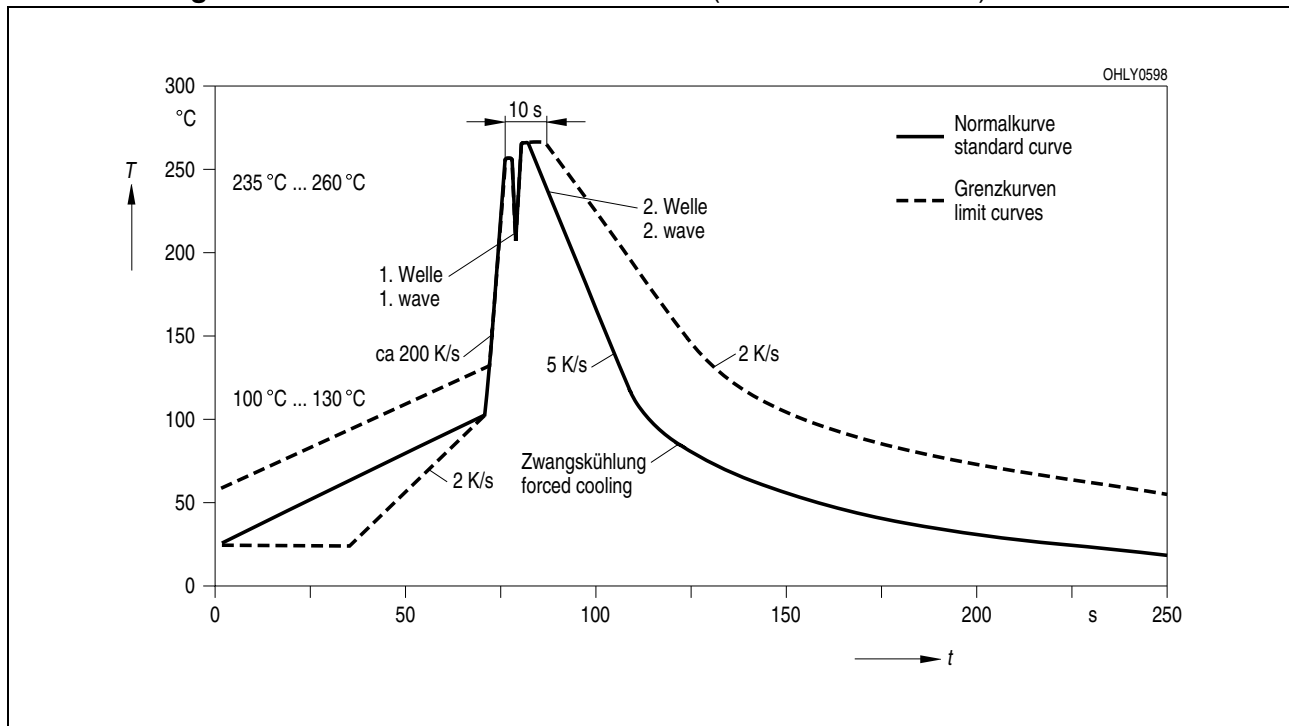
Maßzeichnung
Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
(acc. to CECC 00802)



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